Michael S Fuhrer

List of Publications by Year
in descending order

194 papers	24,565 citations	15466 65 h-index	6818 155 g-index
197 all docs	197 docs citations	197 times ranked	26451 citing authors

#	Article	IF	Citations
1	Formation of a Stable Surface Oxide in MnBi₂Te₄ Thin Films. ACS Applied Materials & Interfaces, 2022, 14, 6102-6108.	4.0	5
2	Defects, band bending and ionization rings in MoS₂. Journal of Physics Condensed Matter, 2022, 34, 174002.	0.7	3
3	Optimizing topological switching in confined 2D-Xene nanoribbons via finite-size effects. Applied Physics Reviews, 2022, 9, .	5.5	7
4	Phase Modulation of Self-Gating in Ionic Liquid-Functionalized InSe Field-Effect Transistors. Nano Letters, 2022, 22, 2270-2276.	4.5	5
5	Atomically Thin Superconductors. Small, 2021, 17, 1904788.	5.2	7
6	Magnesium-intercalated graphene on SiC: Highly n-doped air-stable bilayer graphene at extreme displacement fields. Applied Surface Science, 2021, 541, 148612.	3.1	11
7	Ultrathin Ga₂O₃ Glass: A Largeâ€Scale Passivation and Protection Material for Monolayer WS₂. Advanced Materials, 2021, 33, e2005732.	11.1	49
8	Progress in Epitaxial Thinâ€Film Na₃Bi as a Topological Electronic Material. Advanced Materials, 2021, 33, e2005897.	11.1	18
9	Overcoming Boltzmannâ€™s Tyranny in a Transistor via the Topological Quantum Field Effect. Nano Letters, 2021, 21, 3155-3161.	4.5	36
10	Hybridized Hyperbolic Surface Phonon Polaritons at Î±-MoO₃ and Polar Dielectric Interfaces. Nano Letters, 2021, 21, 3112-3119.	4.5	79
11	Multidimensional analysis of excitonic spectra of monolayers of tungsten disulphide: toward computer-aided identification of structural and environmental perturbations of 2D materials. Machine Learning: Science and Technology, 2021, 2, 025021.	2.4	7
12	Efficient and Tunable Reflection of Phonon Polaritons at Builtâ€In Intercalation Interfaces. Advanced Materials, 2021, 33, e2008070.	11.1	16
13	Bulk transport paths through defects in floating zone and Al flux grown <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mrow><mml:mi>SmB</mml:mi></mml:mrow><mml:mn>6</mml:mn> Physical Review Materials, 2021, 5, .	3.0	9
14	Recent Progress in Proximity Coupling of Magnetism to Topological Insulators. Advanced Materials, 2021, 33, e2007795.	11.1	36
15	Unidirectional magnetotransport of linearly dispersing topological edge states. Physical Review B, 2021, 104, .	1.1	1
16	Crossover from 2D Ferromagnetic Insulator to Wide Band Gap Quantum Anomalous Hall Insulator in Ultrathin MnBi₂Te₄. ACS Nano, 2021, 15, 13444-13452.	7.3	31
17	Recent Progress in Proximity Coupling of Magnetism to Topological Insulators (Adv. Mater. 33/2021). Advanced Materials, 2021, 33, 2170262.	11.1	2
18	Carrier transport theory for twisted bilayer graphene in the metallic regime. Nature Communications, 2021, 12, 5737.	5.8	17

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19	Increasing the Rate of Magnesium Intercalation Underneath Epitaxial Graphene on 6Hâ€SiC(0001). Advanced Materials Interfaces, 2021, 8, 2101598.	1.9	6
20	p-Type Epitaxial Graphene on Cubic Silicon Carbide on Silicon for Integrated Silicon Technologies. ACS Applied Nano Materials, 2020, 3, 830-841.	2.4	18
21	High-Performance Logic and Memory Devices Based on a Dual-Gated MoS₂ Architecture. ACS Applied Electronic Materials, 2020, 2, 111-119.	2.0	26
22	Disentangling the effects of doping, strain and disorder in monolayer WS₂ by optical spectroscopy. 2D Materials, 2020, 7, 025008.	2.0	28
23	Freestanding n-Doped Graphene via Intercalation of Calcium and Magnesium into the Buffer Layerâ€“SiC(0001) Interface. Chemistry of Materials, 2020, 32, 6464-6482.	3.2	28
24	Importance of interactions for the band structure of the topological Dirac semimetal <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi mathvariant="normal">Na</mml:mi><mml:mn>3</mml:mn></mml:msub><mml:mi>Bi</mml:mi></mml:mrow></mml:math>. Physical Review B, 2020, 102, .	1.1	7
25	Quantum Transport in Air-Stable Na₃Bi Thin Films. ACS Applied Materials & Interfaces, 2020, 12, 35542-35546.	4.0	7
26	Helical Edge Transport in Millimeter-Scale Thin Films of Na₃Bi. Nano Letters, 2020, 20, 6306-6312.	4.5	13
27	Quantum Anomalous Hall Effect in Magnetic Doped Topological Insulators and Ferromagnetic Spinâ€Gapless Semiconductorsâ€”A Perspective Review. Small, 2020, 16, e1904322.	5.2	33
28	Dirac-point photocurrents due to the photothermoelectric effect in non-uniform graphene devices. Nature Nanotechnology, 2020, 15, 241-243.	15.6	7
29	Flexible two-dimensional indium tin oxide fabricated using a liquid metal printing technique. Nature Electronics, 2020, 3, 51-58.	13.1	161
30	Electronic Band Structure of In-Plane Ferroelectric van der Waals Î²â€²-In₂Se₃. ACS Applied Electronic Materials, 2020, 2, 213-219.	2.0	26
31	Oxidation of Monolayer WS₂ in Ambient Is a Photoinduced Process. Nano Letters, 2019, 19, 5205-5215.	4.5	66
32	Selective control of surface spin current in topological pyrite-type OsX2 (Xâ€‰=â€‰Se, Te) crystals. Npj Quantum Materials, 2019, 4, .	1.8	8
33	Reliable Synthesis of Largeâ€Area Monolayer WS₂ Single Crystals, Films, and Heterostructures with Extraordinary Photoluminescence Induced by Water Intercalation. Advanced Optical Materials, 2018, 6, 1701347.	3.6	28
34	Thermoelectric properties and performance of flexible reduced graphene oxide films up to 3,000 K. Nature Energy, 2018, 3, 148-156.	19.8	96
35	Long range intrinsic ferromagnetism in two dimensional materials and dissipationless future technologies. Applied Physics Reviews, 2018, 5, .	5.5	119
36	Electric-field-tuned topological phase transition in ultrathin Na3Bi. Nature, 2018, 564, 390-394.	13.7	155

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37	Room temperature in-plane ferroelectricity in van der Waals In ₂ Se ₃. Science Advances, 2018, 4, eaar7720.	4.7	224
38	Terahertz detection in 2D materials. , 2018, , .		1
39	Solid source growth of graphene with Niâ€“Cu catalysts: towards high qualityin situgraphene on silicon. Journal Physics D: Applied Physics, 2017, 50, 095302.	1.3	20
40	Electrochemically Prepared Polycrystalline Copper Surface for the Growth of Hexagonal Boron Nitride. Crystal Growth and Design, 2017, 17, 1669-1678.	1.4	9
41	Direct Observation of 2D Electrostatics and Ohmic Contacts in Template-Grown Graphene/WS₂ Heterostructures. ACS Nano, 2017, 11, 2785-2793.	7.3	74
42	Roomâ€Temperature Singleâ€Photon Emission from Oxidized Tungsten Disulfide Multilayers. Advanced Optical Materials, 2017, 5, 1600939.	3.6	27
43	Polypyridyl Iron Complex as a Hole-Transporting Material for Formamidinium Lead Bromide Perovskite Solar Cells. ACS Energy Letters, 2017, 2, 1855-1859.	8.8	17
44	Temperature-dependent <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>n</mml:mi><mml:mtext>â^'</mml:mtext><mml:mi>p</mml:mi></mml:mrow></mml:math> transition in a three-dimensional Dirac semimetal <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Na</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> thin film. Physical Review B, 2017, 96, .	1.1	9
45	Observation of Effective Pseudospin Scattering in ZrSiS. Nano Letters, 2017, 17, 7213-7217.	4.5	29
46	Spatial charge inhomogeneity and defect states in topological Dirac semimetal thin films of Na ₃ Bi. Science Advances, 2017, 3, eaao6661.	4.7	15
47	Electrostatic modulation of the electronic properties of Dirac semimetal <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Na</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> thin films. Physical Review Materials, 2017, 1, .	3.1	16
48	Facilitating Quantitative Analysis of Atomic Scale 4D STEM Datasets. Microscopy and Microanalysis, 2016, 22, 474-475.	0.2	1
49	Catastrophic degradation of the interface of epitaxial silicon carbide on silicon at high temperatures. Applied Physics Letters, 2016, 109, .	1.5	15
50	Tunable Ultrafast Thermal Relaxation in Graphene Measured by Continuous-Wave Photomixing. Physical Review Letters, 2016, 117, 257401.	2.9	16
51	Graphene plasmonics for terahertz photonics. , 2016, , .		0
52	Electronic Properties of High-Quality Epitaxial Topological Dirac Semimetal Thin Films. Nano Letters, 2016, 16, 3210-3214.	4.5	47
53	Two dimensional and layered transition metal oxides. Applied Materials Today, 2016, 5, 73-89.	2.3	400
54	Practical aspects of diffractive imaging using an atomic-scale coherent electron probe. Ultramicroscopy, 2016, 169, 107-121.	0.8	27

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55	Tuning two-dimensional nanomaterials by intercalation: materials, properties and applications. Chemical Society Reviews, 2016, 45, 6742-6765.	18.7	363
56	Reductive exfoliation of substoichiometric MoS₂bilayers using hydrazine salts. Nanoscale, 2016, 8, 15252-15261.	2.8	24
57	Cobalt Polypyridyl Complexes as Transparent Solutionâ€Processable Solidâ€State Charge Transport Materials. Advanced Energy Materials, 2016, 6, 1600874.	10.2	25
58	Breakdown of compensation and persistence of nonsaturating magnetoresistance in gated<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>WT</mml:mi><mml:msub><mml:mi mathvariant="normal">e</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math>thin flakes. Physical Review B, 2016, 93, .	1.1	49
59	Molecular Doping the Topological Dirac Semimetal Na₃Bi across the Charge Neutrality Point with F4-TCNQ. ACS Applied Materials & Interfaces, 2016, 8, 16412-16418.	4.0	21
60	Structure retrieval with fast electrons using segmented detectors. Physical Review B, 2016, 93, .	1.1	24
61	Measuring the Complex Optical Conductivity of Graphene by Fabry-PÃ©rot Reflectance Spectroscopy. Scientific Reports, 2016, 6, 34166.	1.6	21
62	Strain Relaxation of Monolayer WS₂ on Plastic Substrate. Advanced Functional Materials, 2016, 26, 8707-8714.	7.8	97
63	Evolution of electronic states in n-type copper oxide superconductor via electric double layer gating. Scientific Reports, 2016, 6, 26642.	1.6	21
64	Response to â€œComment on â€˜Catastrophic degradation of the interface of epitaxial silicon carbide on silicon at high temperaturesâ€™â€•[Appl. Phys. Lett. 109, 196101 (2016)]. Applied Physics Letters, 2016, 109, 196102.	1.5	2
65	Nonlinear optical frequency mixing response of single and multilayer graphene. Optics Letters, 2016, 41, 1122.	1.7	9
66	Acoustically-Driven Trion and Exciton Modulation in Piezoelectric Two-Dimensional MoS₂. Nano Letters, 2016, 16, 849-855.	4.5	91
67	Terahertz Plasmon Resonances in Graphene-Filled Subwavelength Metallic Apertures. , 2016, , .		0
68	A simple technique for performing evaporation of quaterthiophene below the melting temperature for vapour phase polymerisation and physical vapour deposition. RSC Advances, 2015, 5, 99806-99811.	1.7	2
69	Observation of topological transition of Fermi surface from a spindle torus to a torus in bulk Rashba spin-split BiTeCl. Physical Review B, 2015, 92, .	1.1	69
70	Neutral-current Hall effects in disordered graphene. Physical Review B, 2015, 92, .	1.1	38
71	Electronic transport properties of Ir-decorated graphene. Scientific Reports, 2015, 5, 15764.	1.6	24
72	Pulsed Near-IR Photoresponse in a Bi-metal Contacted Graphene Photodetector. Scientific Reports, 2015, 5, 14803.	1.6	7

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73	Self-Limiting Layer-by-Layer Oxidation of Atomically Thin WSe₂. Nano Letters, 2015, 15, 2067-2073.	4.5	204
74	Helicity-Resolved Raman Scattering of MoS₂, MoSe₂, WS₂, and WSe₂ Atomic Layers. Nano Letters, 2015, 15, 2526-2532.	4.5	241
75	Creating a Stable Oxide at the Surface of Black Phosphorus. ACS Applied Materials & Interfaces, 2015, 7, 14557-14562.	4.0	318
76	Profound Effect of Substrate Hydroxylation and Hydration on Electronic and Optical Properties of Monolayer MoS₂. Nano Letters, 2015, 15, 3096-3102.	4.5	45
77	Tuning Bulk and Surface Conduction in the Proposed Topological Kondo Insulator<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>SmB</mml:mi><mml:mn>6</mml:mn></mml:msub></mml:math>. Physical Review Letters, 2015, 114, 096601.	2.9	115
78	Synthesis and Transfer of Large-Area Monolayer WS₂ Crystals: Moving Toward the Recyclable Use of Sapphire Substrates. ACS Nano, 2015, 9, 6178-6187.	7.3	200
79	Plasmon-Enhanced Terahertz Photodetection in Graphene. Nano Letters, 2015, 15, 4295-4302.	4.5	94
80	Tunable Terahertz Hybrid Metalâ€“Graphene Plasmons. Nano Letters, 2015, 15, 7099-7104.	4.5	135
81	Characterization of Graphene Photothermoelectric Detector via Two-wave Mixing Technique. , 2015, , .		0
82	The positive piezoconductive effect in graphene. Nature Communications, 2015, 6, 8119.	5.8	43
83	In Situ Investigations of Liâ€MoS₂ with Planar Batteries. Advanced Energy Materials, 2015, 5, 1401742.	10.2	87
84	Air-stable doping of Bi<inf>2</inf>Se<inf>3</inf> by MoO<inf>3</inf> into the topological regime. , 2014, , .		0
85	Characterization of Fast Temporal Photoreponse in a Broadband Graphene Photodetector. , 2014, , .		0
86	Carbon impurities on graphene synthesized by chemical vapor deposition on platinum. Journal of Applied Physics, 2014, 116, 044303.	1.1	15
87	Thickness and growth-condition dependence of in-situ mobility and carrier density of epitaxial thin-film Bi2Se3. Applied Physics Letters, 2014, 105, 173506.	1.5	18
88	Ambipolar Surface State Thermoelectric Power of Topological Insulator Bi₂Se₃. Nano Letters, 2014, 14, 1701-1706.	4.5	56
89	Air-Stable Electron Depletion of Bi₂Se₃ Using Molybdenum Trioxide into the Topological Regime. ACS Nano, 2014, 8, 6400-6406.	7.3	29
90	Disorder-Induced Magnetoresistance in a Two-Dimensional Electron System. Physical Review Letters, 2014, 113, 047206.	2.9	47

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91	Stability and Surface Reconstruction of Topological Insulator Bi₂Se₃ on Exposure to Atmosphere. Journal of Physical Chemistry C, 2014, 118, 20413-20419.	1.5	62
92	Sensitive room-temperature terahertz detection via the photothermoelectric effect in graphene. Nature Nanotechnology, 2014, 9, 814-819.	15.6	474
93	Approaching the limits of transparency and conductivity in graphitic materials through lithium intercalation. Nature Communications, 2014, 5, 4224.	5.8	213
94	Direct Imaging of Charged Impurity Density in Common Graphene Substrates. Nano Letters, 2013, 13, 3576-3580.	4.5	70
95	Measurement of mobility in dual-gated MoS2 transistors. Nature Nanotechnology, 2013, 8, 146-147.	15.6	443
96	Critical Mass in Graphene. Science, 2013, 340, 1413-1414.	6.0	18
97	Anisotropic Etching of Atomically Thin MoS₂. Journal of Physical Chemistry C, 2013, 117, 25643-25649.	1.5	176
98	High mobility ambipolar MoS2 field-effect transistors: Substrate and dielectric effects. Applied Physics Letters, 2013, 102, .	1.5	669
99	Photothermal Response in Dual-Gated Bilayer Graphene. Physical Review Letters, 2013, 110, 247402.	2.9	41
100	Coherent topological transport on the surface of Bi2Se3. Nature Communications, 2013, 4, 2040.	5.8	116
101	Broadband Responsivity of a Graphene Photodetector. , 2013, , .		0
102	In situ monitoring of resistivity and carrier concentration during molecular beam epitaxy of topological insulator Bi₂Se₃. Proceedings of SPIE, 2013, , .	0.8	2
103	Thin-film barristor: A gate-tunable vertical graphene-pentacene device. Physical Review B, 2013, 88, .	1.1	51
104	Electrical detection of CF3Cl phase transitions on graphene. Applied Physics Letters, 2013, 103, 201606.	1.5	2
105	Reply to "Origin of logarithmic resistance correction in graphene". Nature Physics, 2012, 8, 353-353.	6.5	15
106	Surface conduction of topological Dirac electrons in bulk insulating Bi2Se3. Nature Physics, 2012, 8, 459-463.	6.5	330
107	Potential Steps at C60â€“TiOPcâ€“Ag(111) Interfaces: Ultrahigh-Vacuumâ€“Noncontact Scanning Probe Metrology. Nano Letters, 2012, 12, 2859-2864.	4.5	6
108	â€œThe Princess and the Peaâ€•at the Nanoscale: Wrinkling and Delamination of Graphene on Nanoparticles. Physical Review X, 2012, 2, .	2.8	35

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109	Dual-gated bilayer graphene hot-electron bolometer. Nature Nanotechnology, 2012, 7, 472-478.	15.6	409
110	Intrinsic Electron-Phonon Resistivity of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>Bi</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi>Se</mml:mi><mml:mn the Topological Regime. Physical Review Letters, 2012, 109, 166801.	2.9	73
111	Universal Conductance Fluctuations in Dirac Materials in the Presence of Long-range Disorder. Physical Review Letters, 2012, 109, 096801.	2.9	53
112	Charge Inhomogeneity Determines Oxidative Reactivity of Graphene on Substrates. ACS Nano, 2012, 6, 8335-8341.	7.3	62
113	Layer Number and Stacking Sequence Imaging of Few-Layer Graphene by Transmission Electron Microscopy. Nano Letters, 2012, 12, 4635-4641.	4.5	64
114	Topological Insulator Quantum Dot with Tunable Barriers. Nano Letters, 2012, 12, 469-472.	4.5	50
115	Towards spin injection from silicon into topological insulators: Schottky barrier between Si and Bi2Se3. Applied Physics Letters, 2012, 101, .	1.5	28
116	High-Quality Uniform Dry Transfer of Graphene to Polymers. Nano Letters, 2012, 12, 102-107.	4.5	128
117	Single Carbon Nanotube Schottky Diode Microwave Rectifiers. IEEE Transactions on Microwave Theory and Techniques, 2011, 59, 2726-2732.	2.9	15
118	Insulating Behavior in Ultrathin Bismuth Selenide Field Effect Transistors. Nano Letters, 2011, 11, 1925-1927.	4.5	152
119	Proposal for a topological plasmon spin rectifier. Applied Physics Letters, 2011, 98, .	1.5	37
120	Correlated Charged Impurity Scattering in Graphene. Physical Review Letters, 2011, 107, 206601.	2.9	142
121	Raman and optical characterization of multilayer turbostratic graphene grown via chemical vapor deposition. Journal of Applied Physics, 2011, 110, .	1.1	138
122	Characterization of the electrical contact between a conductive atomic force microscope cantilever and a carbon nanotube. Journal of Applied Physics, 2011, 110, 054305.	1.1	8
123	Tunable Kondo effect in graphene with defects. Nature Physics, 2011, 7, 535-538.	6.5	353
124	Polymeric semiconductor/graphene hybrid field-effect transistors. Organic Electronics, 2011, 12, 1471-1476.	1.4	60
125	Kelvin probe microscopy and electronic transport in graphene on SiC(0001) in the minimum conductivity regime. Applied Physics Letters, 2011, 98, .	1.5	38
126	Graphene: Materially Better Carbon. MRS Bulletin, 2010, 35, 289-295.	1.7	191

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127	Ribbons piece-by-piece. Nature Materials, 2010, 9, 611-612.	13.3	14
128	Optimizing transistor performance of percolating carbon nanotube networks. Applied Physics Letters, 2010, 97, 043111.	1.5	37
129	High-Fidelity Conformation of Graphene to<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>SiO</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:math>Topographic Features. Physical Review Letters, 2010, 105, 215504.	2.9	118
130	Charged impurity scattering in bilayer graphene. Physical Review B, 2010, 82, .	1.1	81
131	Charge Transport in Dual Gated Bilayer Graphene with Corbino Geometry. Nano Letters, 2010, 10, 4521-4525.	4.5	76
132	Carbon Nanotubes and Graphene for High-Frequency Electronics - Invited. ECS Meeting Abstracts, 2009, , .	0.0	0
133	Controlled growth, patterning and placement of carbon nanotube thin films. , 2009, , .		0
134	Frequency-dependent complex conductivity of an organic thin-film transistor. Applied Physics Letters, 2009, 94, 232103.	1.5	7
135	Carbon conductor corrupted. Nature, 2009, 458, 38-39.	13.7	12
136	Journal club. Nature, 2009, 459, 1037-1037.	13.7	7
137	Solution-processed single walled carbon nanotube electrodes for organic thin-film transistors. Organic Electronics, 2009, 10, 1556-1561.	1.4	45
138	Scattering mechanisms in graphene. , 2009, , .		0
139	Defect Scattering in Graphene. Physical Review Letters, 2009, 102, 236805.	2.9	566
140	Tuning the Effective Fine Structure Constant in Graphene: Opposing Effects of Dielectric Screening on Short- and Long-Range Potential Scattering. Physical Review Letters, 2008, 101, 146805.	2.9	321
141	Charge transport and inhomogeneity near the minimum conductivity point in graphene. Physical Review B, 2008, 77, .	1.1	153
142	Intrinsic and extrinsic performance limits of graphene devices on SiO2. Nature Nanotechnology, 2008, 3, 206-209.	15.6	2,730
143	Charged-impurity scattering in graphene. Nature Physics, 2008, 4, 377-381.	6.5	1,318
144	Origins of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^•</mml:mo><mml:mi>f</mml:mi></mml:mrow></mml:math>noise in individual semiconducting carbon nanotube field-effect transistors. Physical Review B, 2008, 77, .	1.1	43

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145	Microwave rectification by a carbon nanotube Schottky diode. Applied Physics Letters, 2008, 93, .	1.5	32
146	A Versatile Biomolecular Charge-Based Sensor Using Oxide-Gated Carbon Nanotube Transistor Arrays. IEEE Sensors Journal, 2008, 8, 655-660.	2.4	9
147	Facile fabrication of suspended as-grown carbon nanotube devices. Applied Physics Letters, 2008, 93, 113112.	1.5	29
148	Optical measurement of thermal transport in suspended carbon nanotubes. Applied Physics Letters, 2008, 92, .	1.5	91
149	Density Inhomogeneity Driven Percolation Metal-Insulator Transition and Dimensional Crossover in Graphene Nanoribbons. Physical Review Letters, 2008, 101, 046404.	2.9	98
150	Poly(3-hexylthiophene) thin-film transistors with variable polymer dielectrics for transfer-printed flexible electronics. Journal of Applied Physics, 2008, 104, .	1.1	25
151	Fabrication and characterization of suspended carbon nanotubes. , 2007, , .		0
152	Transparent organic field-effect transistors with carbon nanotube electrodes. , 2007, , .		0
153	Organic and carbon-based electronics printed onto flexible substrates. , 2007, , .		0
154	Transfer printing as a method for fabricating hybrid devices on flexible substrates. , 2007, 6658, 141.		8
155	Gate-tunable graphene spin valve. Applied Physics Letters, 2007, 91, .	1.5	259
156	Transmission line impedance of carbon nanotube thin films for chemical sensing. Applied Physics Letters, 2007, 90, 123510.	1.5	15
157	Realization and electrical characterization of ultrathin crystals of layered transition-metal dichalcogenides. Journal of Applied Physics, 2007, 101, 014507.	1.1	512
158	Atomic Structure of Graphene on SiO2. Nano Letters, 2007, 7, 1643-1648.	4.5	1,392
159	Four-terminal measurements of SWNTs using MWNTs as voltage electrodes. Physica Status Solidi (B): Basic Research, 2006, 243, 3399-3402.	0.7	0
160	Current-carrying capacity of semiconducting carbon nanotubes. Physica Status Solidi (B): Basic Research, 2006, 243, 3403-3407.	0.7	6
161	Tuning from Thermionic Emission to Ohmic Tunnel Contacts via Doping in Schottky-Barrier Nanotube Transistors. Nano Letters, 2006, 6, 2158-2162.	4.5	57
162	Patterned Carbon Nanotube Thin-Film Transistors with Transfer-Print Assembly. Materials Research Society Symposia Proceedings, 2006, 963, 1.	0.1	9

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163	Hoogeâ€™s constant for carbon nanotube field effect transistors. Applied Physics Letters, 2006, 88, 203116.	1.5	89
164	Electrodes for carbon nanotube devices by focused electron beam induced deposition of gold. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 3174.	1.6	78
165	Nanotransfer printing of organic and carbon nanotube thin-film transistors on plastic substrates. Applied Physics Letters, 2005, 86, 163101.	1.5	114
166	Electric-Field-Dependent Charge-Carrier Velocity in Semiconducting Carbon Nanotubes. Physical Review Letters, 2005, 95, 236803.	2.9	80
167	Bulk vortex matter inBi2Sr2CaCu2O8+Î´using Corbinol disk contacts. Physical Review B, 2005, 71, .	1.1	1
168	Four-Point Resistance of Individual Single-Wall Carbon Nanotubes. Physical Review Letters, 2005, 95, 196802.	2.9	108
169	Temperature control of electromigration to form gold nanogap junctions. Applied Physics Letters, 2005, 87, 263101.	1.5	103
170	Near-perfect conduction through a ferrocene-based molecular wire. Physical Review B, 2005, 71, .	1.1	121
171	Gate-Field-Induced Schottky Barrier Lowering in a Nanotube Field-Effect Transistor. AIP Conference Proceedings, 2004, , .	0.3	0
172	High-performance carbon nanotube transistors on SrTiO3/Si substrates. Applied Physics Letters, 2004, 84, 1946-1948.	1.5	70
173	Properties and applications of high-mobility semiconducting nanotubes. Journal of Physics Condensed Matter, 2004, 16, R553-R580.	0.7	135
174	A photolithographic process for fabrication of devices with isolated single-walled carbon nanotubes. Nanotechnology, 2004, 15, 1475-1478.	1.3	33
175	Extraordinary Mobility in Semiconducting Carbon Nanotubes. Nano Letters, 2004, 4, 35-39.	4.5	1,368
176	Rotational actuators based on carbon nanotubes. Nature, 2003, 424, 408-410.	13.7	1,098
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